

# PHEMT GaAs IC Transfer Switch DC–2 GHz



AS172-73

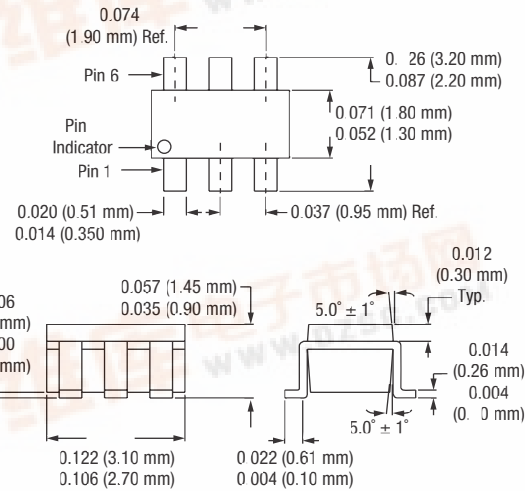
## Features

- High Linearity (+50 dBm IP3 @ 0.9 GHz) @ 3 V
- Low Insertion Loss (0.4 dB @ 0.9 GHz)
- Isolation (20 dB @ 0.9 GHz)
- Simultaneous T/R Switching

## Description

The AS172-73 is a PHEMT GaAs IC 4 port switch designed to combine T/R and antenna changeover switching capability within one device. This switch has two controls and is ideal for applications requiring low power consumption. The AS172-73 has excellent performance to 2 GHz making it suitable for dual-band handset designs.

## SOT-6



## Electrical Specifications at 25°C (0, +3 V)

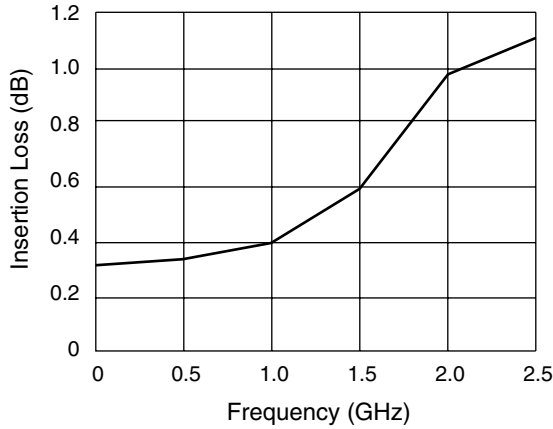
Parameter <sup>1</sup>	Frequency <sup>2</sup>	T <sub>X</sub> -J <sub>1</sub> or R <sub>X</sub> -J <sub>1</sub>			Unit
		Min.	Typ.	Max.	
Insertion Loss <sup>3</sup>	DC–0.5 GHz		0.30	0.40	dB
	DC–1.0 GHz		0.40	0.50	dB
	DC–2.0 GHz		0.95	1.20	dB
Isolation	DC–0.5 GHz	23	25		dB
	DC–1.0 GHz	16	18		dB
	DC–2.0 GHz	11	13		dB
VSWR <sup>4</sup>	DC–1.0 GHz		1.1:1		
	DC–2.0 GHz		1.4:1		

## Operating Characteristics at 25°C (0, +3 V)

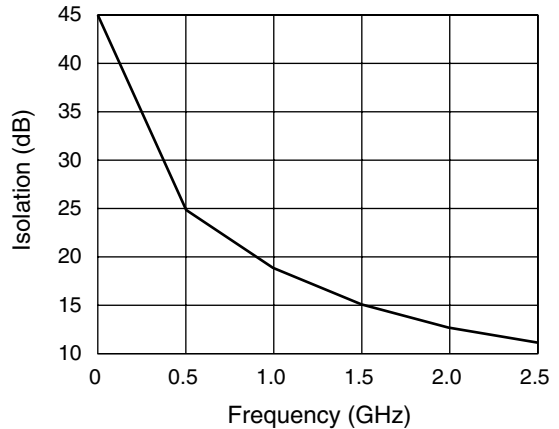
Parameter	Condition	Frequency	Min.	Typ.	Max.	Unit
Switching Characteristics <sup>5</sup>	Rise, Fall (10/90% or 90/10% RF)			50		ns
	On, Off (50% CTL to 90/10% RF)			100		ns
	Video Feedthru				50	
Input Power for 1 dB Compression	0/+3 V	0.5–2.0 GHz		+34		dBm
Intermodulation Intercept Point (IP3)	For Two-tone Input Power +15 dBm 0/+3 V	0.5–2.0 GHz		+50		dBm
2nd Harmonic	30 dBm	1.0 GHz		+72		dBc
3rd Harmonic	30 dBm	1.0 GHz		+65		dBc
Control Voltages	V <sub>Low</sub> = 0 to 0.2 V @ 20 μA Max. V <sub>High</sub> = +3 V @ 100 μA Max. to +5 V @ 200 μA Max. V <sub>S</sub> = V <sub>High</sub> ± 0.2 V					

1. All measurements made in a 50 Ω system, unless otherwise specified.  
 2. DC = 300 kHz.  
 3. Insertion loss changes by 0.003 dB/°C.  
 4. Insertion loss state.  
 5. Video feedthru measured with 1 ns risetime pulse and 500 MHz bandwidth.

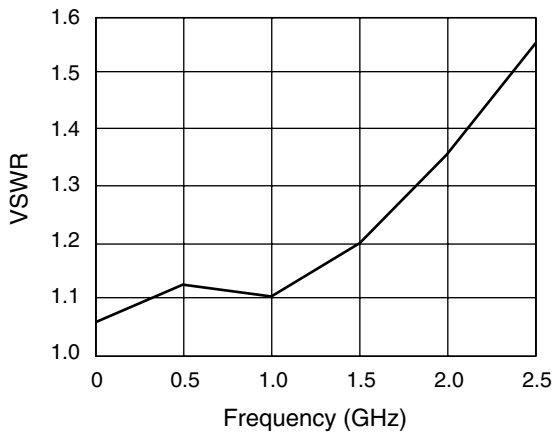
**Typical Performance Data (0, +3 V)**



**Insertion Loss vs. Frequency**



**Isolation vs. Frequency**



**VSWR vs. Frequency**

**Absolute Maximum Ratings**

Characteristic	Value
RF Input Power	2 W > 500 MHz 0/+7 V Control
Control Voltage	-0.2 V, +8 V
Operating Temperature	-40°C to +85°C
Storage Temperature	-50°C to +150°C
$\theta_{JC}$	25°C/W

**Truth Table**

**Negative Operation**

V <sub>1</sub>	V <sub>2</sub>	T <sub>X</sub> -J <sub>2</sub> , R <sub>X</sub> -J <sub>1</sub>	T <sub>X</sub> -J <sub>1</sub> , R <sub>X</sub> -J <sub>2</sub>
0	-3	Insertion Loss	Isolation
-3	0	Isolation	Insertion Loss

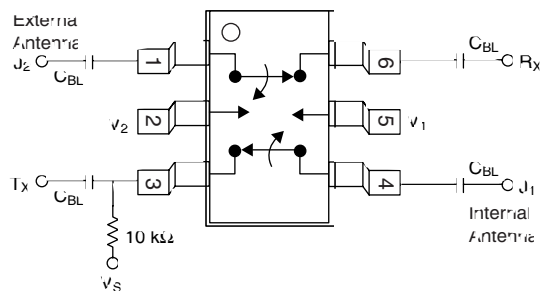
**Positive Operation**

V <sub>1</sub>	V <sub>2</sub>	T <sub>X</sub> -J <sub>2</sub> , R <sub>X</sub> -J <sub>1</sub>	T <sub>X</sub> -J <sub>1</sub> , R <sub>X</sub> -J <sub>2</sub>
V <sub>High</sub>	0	Insertion Loss	Isolation
0	V <sub>High</sub>	Isolation	Insertion Loss

V<sub>High</sub> = +3 to +8 V (V<sub>S</sub> = V<sub>High</sub> ± 0.2 V).

**Pin Out**

**Positive Operation**



DC blocking capacitors (C<sub>BL</sub>) and biasing resistor must be supplied externally for positive voltage operation.

C<sub>BL</sub> = 100 pF for operation >500 MHz.